

IN THE CLAIMS:

Claims 1-13, and 15-18 have been amended. All of the pending claims 1 through 18 are presented below. This listing of claims will replace all prior versions and listings of claims in the application. Please enter these claims as amended.

1. (Currently Amended) An intermediate structure of a post-probe tested semiconductor device comprising:
at least one opened fuse structure; and
a metal feature plated on a first metal structure of ~~said~~ the intermediate structure, ~~said~~ the metal feature formed after probe testing, wherein ~~said~~ the at least one opened fuse structure is not reformed by a metal of ~~said~~ the metal feature.
2. (Currently Amended) The intermediate structure of claim 1, wherein ~~said~~ the metal feature comprises an electrolessly plated metal feature.
3. (Currently Amended) The intermediate structure of claim 1, wherein ~~said~~ the metal feature is a metal layer, an interconnect cap, a redistribution layer, or a bond pad.
4. (Currently Amended) The intermediate structure of claim 3, wherein ~~said~~ the metal feature is ~~said~~ the metal layer.
5. (Currently Amended) The intermediate structure of claim 1, wherein ~~said~~ the metal feature comprises nickel, palladium, gold, tin, silver, or copper.
6. (Currently Amended) The intermediate structure of claim 5, wherein ~~said~~ the metal feature comprises nickel.

7. (Currently Amended) The intermediate structure of claim 1, wherein ~~said~~ the first metal structure comprises at least one bond pad.

8. (Currently Amended) The intermediate structure of claim 1, wherein ~~said~~ the intermediate structure is an intermediate structure of an SRAM or FLASH memory chip.

9. (Currently Amended) An intermediate structure of a post-probe tested semiconductor device produced by a method comprising:
providing ~~said~~ the intermediate structure comprising an exposed metal structure and at least one opened fuse;
adjusting a concentration of stabilizer in an electroless plating solution; and
electrolessly plating a metal feature on ~~said~~ the exposed metal structure without depositing a metal of ~~said~~ the metal feature on ~~said~~ the at least one opened fuse.

10. (Currently Amended) The intermediate structure of claim 9, wherein ~~said~~ the metal feature is a metal layer, an interconnect cap, a redistribution layer, or a bond pad.

11. (Currently Amended) The intermediate structure of claim 9, wherein ~~said~~ the metal feature comprises nickel, palladium, gold, tin, silver, or copper.

12. (Currently Amended) The intermediate structure of claim 9, wherein ~~said~~ the exposed metal structure comprises at least one bond pad.

13. (Currently Amended) The intermediate structure of claim 9, wherein providing ~~said~~ the intermediate structure comprising an exposed metal structure and at least one opened fuse comprises providing an intermediate structure of an SRAM or FLASH memory chip.

14. (Original) The intermediate structure of claim 9, wherein adjusting a concentration of stabilizer in an electroless plating solution comprises adjusting a concentration of stabilizer selected from the group consisting of compounds of group VI elements, compounds comprising oxygen, heavy metal cations, and unsaturated organic acids.

15. (Currently Amended) The intermediate structure of claim 14, wherein ~~said~~ the compounds of group VI elements comprise compounds of S, Se, or Te.

16. (Currently Amended) The intermediate structure of claim 14, wherein ~~said~~ the compounds comprising oxygen comprise compounds of AsO_2^- , IO_3^- , or MoO_4^- .

17. (Currently Amended) The intermediate structure of claim 14, wherein ~~said~~ the heavy metal cations comprise Sn, Pb, Hg, or Sb.

18. (Currently Amended) The intermediate structure of claim 14, wherein ~~said~~ the unsaturated organic acids comprise maleic acid or itaconic acid.